

Model RFP-100200-4X50-2

Chip Terminations 30 Watts, 50 \(\Omega \)



Features

- DC 3.0 GHz
- 30 Watts
- BeO Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

General Specifications

Resistive Element: Thick film

Substrate: Beryllium oxide ceramic

Terminals: Thick film silver

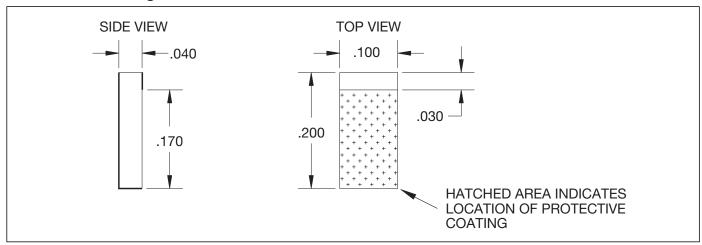
Electrical Specifications

Resistance Value:50 ohms, $\pm 2\%$ Frequency Range:DC - 3.0 GHzPower:30 WattsV.S.W.R.:1.25:1

Notes: Tolerance is ±.010, unless otherwise specified. Operating temperature is -55°C to +150°C (see chart). Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions are in inches.

Specifications subject to change without notice.

Outline Drawing



VER. 12/5/01

Available on Tape and Reel for Pick and Place Manufacturing.

Sales Desk USA: Voice: (800) 544-2414 Fax: (315) 432-9121

Sales Desk Europe: Voice: (+44) 23 92 232392 Fax: (+44) 23 92 251369

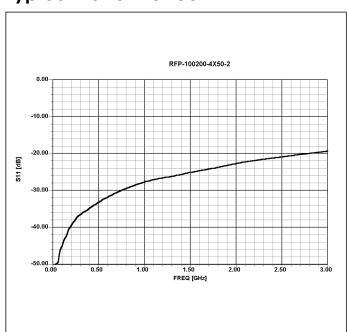


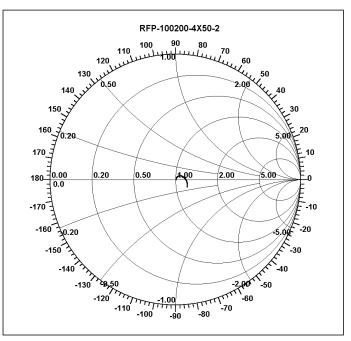
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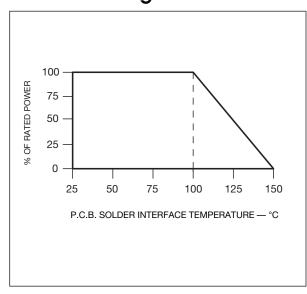


Typical Performance

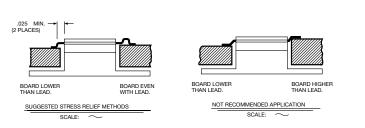




Power Derating



Suggested Mounting Procedures



- 1. Make sure that the devices are mounted on flat surfaces (.001" under the device) to optimize the heat transfer.
- 2. Position device on mounting surface and solder in place using an indalloy type or a 60/40 type solder.
- 3. Solder leads in place using a 60/40 type solder with a controlled temperature iron (700°F).





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